

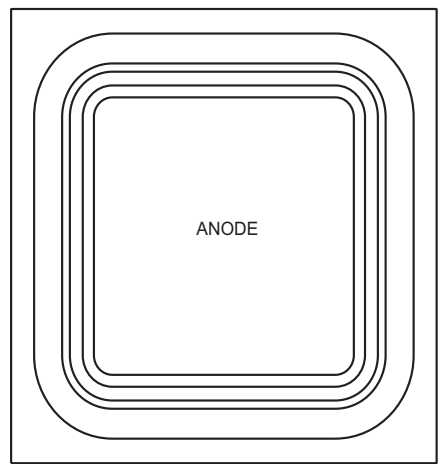
PROCESS CPD96V
Schottky Diode
500mA Low V_F Schottky Diode Chip

CentralTM
Semiconductor Corp.

PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	20 x 20 MILS
Die Thickness	7.1 MILS
Anode Bonding Pad Area	16 x 16 MILS
Top Side Metalization	Al - 20,000Å
Back Side Metalization	Au - 12,000Å

GEOMETRY



BACKSIDE CATHODE

GROSS DIE PER 4 INCH WAFER

28,028

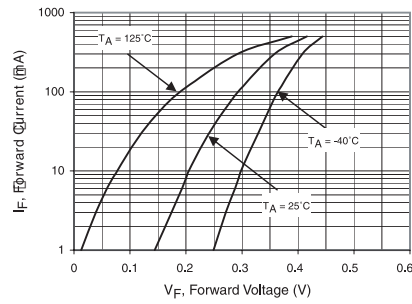
PRINCIPAL DEVICE TYPES

CMLSH05-4

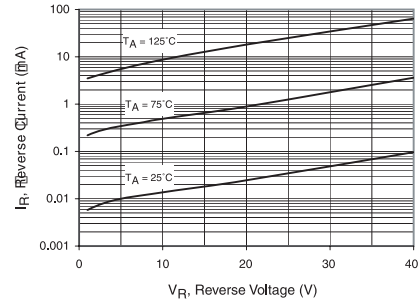
145 Adams Avenue
Hauppauge, NY 11788 USA
Tel: (631) 435-1110
Fax: (631) 435-1824
www.centrasemi.com

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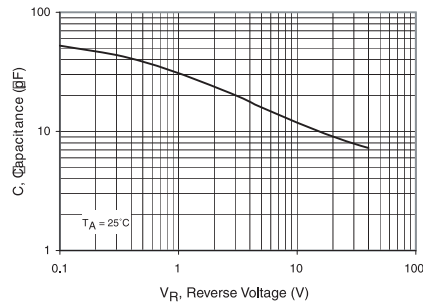
Forward Voltage



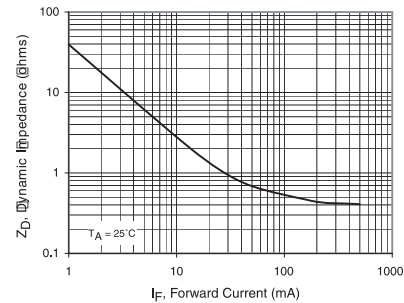
Leakage Current



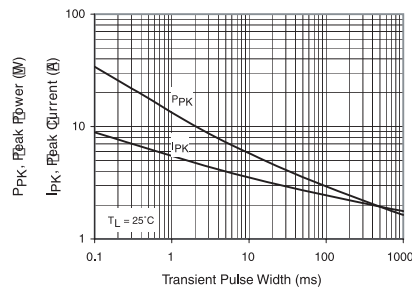
Capacitance



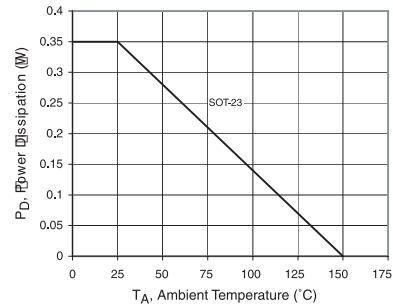
Forward Dynamic Impedance



Transient Peak Power and Peak Current Capacity



Power Derating



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